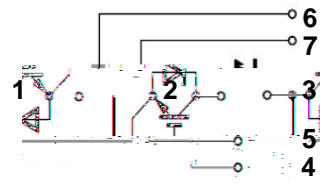


General Description

TRinno IGBT power module provides low conduction and switching losses as well as short circuit ruggedness. It is designed for applications such as Motor Driver, IH , Rectifier and Welder.

Features

- 1200V Field Stop Trench IGBT Technology
- Fast & Soft Recovery Diodes
- Positive Temperature Coefficient
- Short Circuit Withstanding Time : 10 s



Applications

Motor driver, IH(Induction heating), Rectifier, Welder

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit	
Collector-Emitter Voltage	V_{CES}	1200	V	
Gate-Emitter Voltage	V_{GES}	± 20	V	
Continuous Collector Current	I_C	$T_C = 25$	300	A
		$T_C = 100$	150	A
Pulsed Collector Current (Note 1)	I_{CM}	300	A	
Diode Continuous Forward Current	I_F	150	A	
Power Dissipation	P_D	$T_C = 25$	893	W
		$T_C = 100$	357	W
Operating Junction Temperature	T_{vj}	-40 ~ 150		
Storage Temperature Range	T_{STG}	-40 ~ 150		

Notes :

(1) Repetitive rating : Pulse width limited by maximum junction temperature

Thermal Characteristics

Parameter	Symbol	Value	Unit
Maximum Thermal resistance, Junction-to-Case (Per ½ Module)		0.14	K/W
Maximum Thermal resistance, Junction-to-Case (Per ½ Module)		0.54	K/W

Electrical Characteristics of the IGBT $T_{vj}=25^{\circ}\text{C}$, unless otherwise noted

Parameter	Symbol	Test condition	Min.	Typ.	Max.	Unit
OFF						
Collector Emitter Breakdown Voltage	BV_{CES}	$V_{GE} = 0V, I_C = 1mA$	1200	--	--	V
Zero Gate Voltage Collector Current	I_{CES}	$V_{CE} = 1200V, V_{GE} = 0V$	--	--	1	mA
Gate Emitter Leakage Current	I_{GES}	$V_{CE} = 0V, V_{GE} = 20V$	--	--	100	nA
ON						
Gate Emitter Threshold Voltage	$V_{GE(TH)}$	$V_{GE} = V_{CE}, I_C = 150mA$	5.0	--	8.0	V
Collector Emitter Saturation Voltage	$V_{CE(SAT)}$	$V_{GE} = 15V, I_C = 150A, T_{vj} = 25$	--	2.0	2.5	V
		$V_{GE} = 15V, I_C = 150A, T_{vj} = 125$	--	2.3		V
DYNAMIC						
Input Capacitance	C_{IES}	$V_{CE} = 25V,$ $V_{GE} = 0V$ $f = 1MHz$	--	13	--	nF
Output Capacitance	C_{OES}		--	720	--	pF
Reverse Transfer Capacitance	C_{RES}		--	120	--	pF
SWITCHING						
Turn-On Delay Time	$t_{d(on)}$	$V_{CC} = 600V, I_C = 150A$ $R_G = 2, V_{GE} = 15V$ Inductive Load, $T_{vj} = 25$	--	64	--	ns
Rise Time	t_r		--	86	--	ns
Turn-Off Delay Time	$t_{d(off)}$		--	156	--	ns
Fall Time	t_f		--	82	--	ns
Turn-On Switching Loss	E_{ON}		--	13.6	--	mJ
Turn-Off Switching Loss	E_{OFF}		--	6.7	--	mJ
Total Switching Loss	E_{TS}		--	20.3	--	mJ
Turn-On Delay Time	$t_{d(on)}$	$V_{CC} = 600V, I_C = 150A$ $R_G = 2, V_{GE} = 15V$ Inductive Load, $T_{vj} = 125$	--	73	--	ns
Rise Time	t_r		--	88	--	ns
Turn-Off Delay Time	$t_{d(off)}$		--	207	--	ns
Fall Time	t_f		--	94	--	ns
Turn-On Switching Loss	E_{ON}		--	17.8	--	mJ
Turn-Off Switching Loss	E_{OFF}		--	8.5	--	mJ
Total Switching Loss	E_{TS}		--	26.3	--	mJ
Total Gate Charge	Q_g	$V_{CC} = 600V, I_C = 150A$ $V_{GE} = 15V$	--	1185	--	nC
Gate-Emitter Charge	Q_{ge}		--	215	--	nC
Gate-Collector Charge	Q_{gc}		--	505	--	nC
Short Circuit Withstanding Time	t_{SC}	$V_{CC} = 600V, V_{GE} = 15V, T_{vj} = 125$	10	--	--	s



IGBT Characteristics

Fig. 1 Output characteristics

Fig. 2 Saturation voltage characteristics

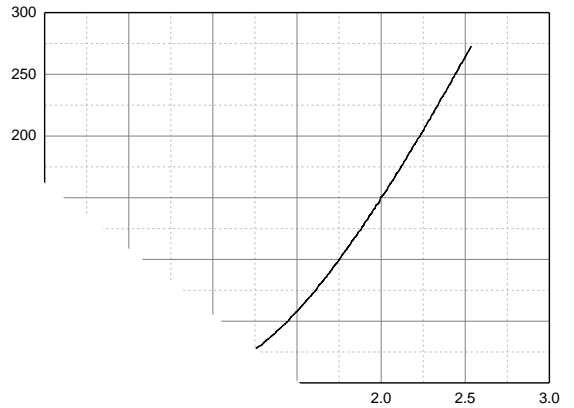


Fig. 3 Switching loss vs. gate resistor

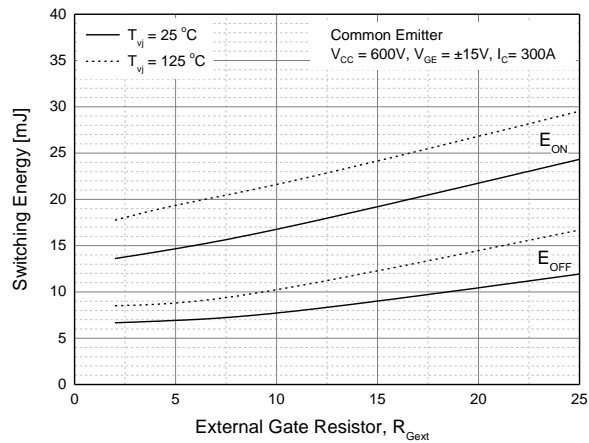


Fig. 4 Switching loss vs. collector current

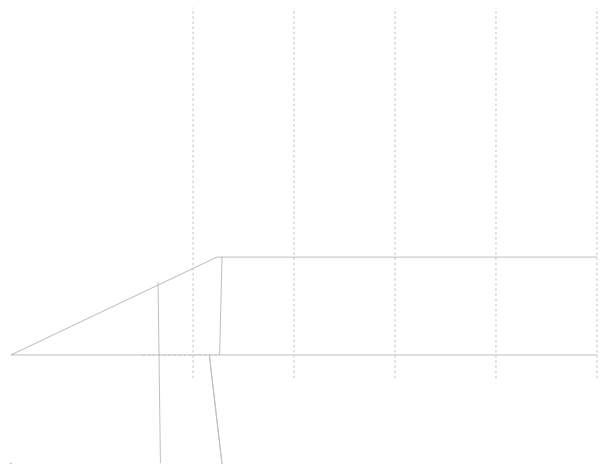
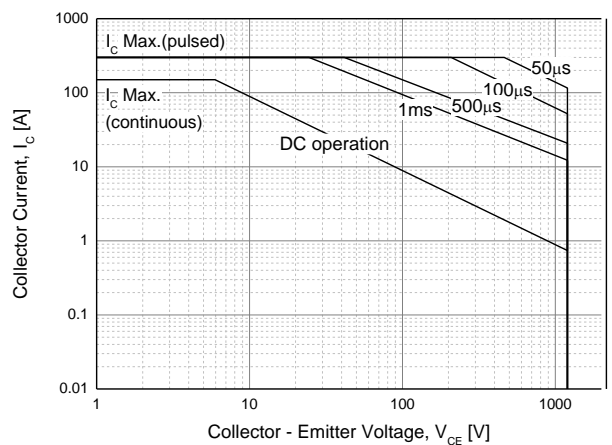
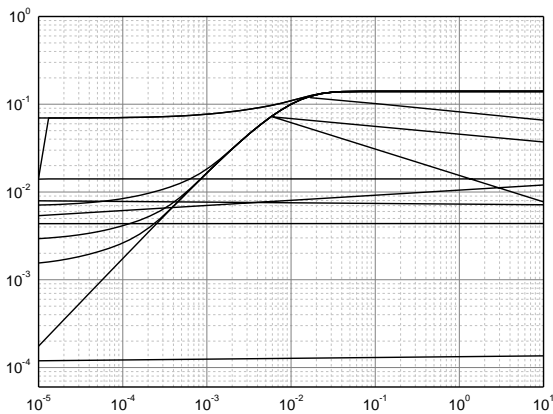


Fig. 5 Transient thermal impedance of IGBT

Fig. 6 SOA



IGBT Characteristics

Fig. 7 RBSOA

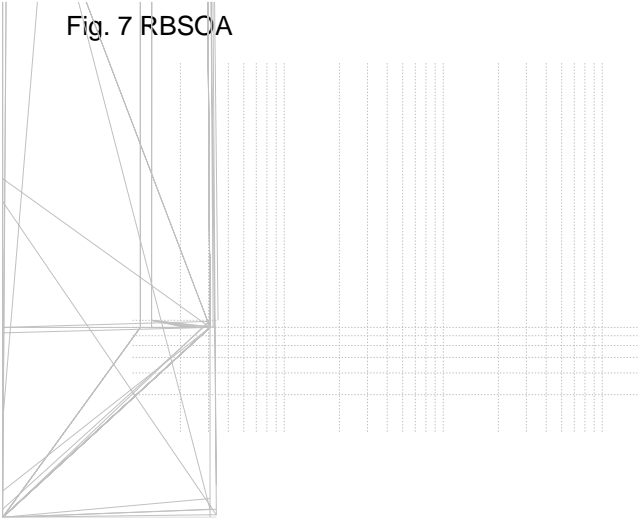


Fig. 8 Load current vs. frequency

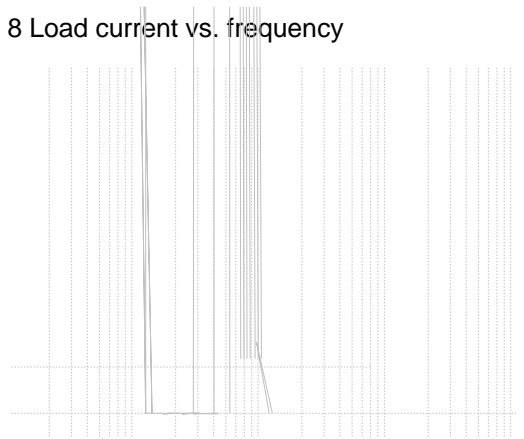
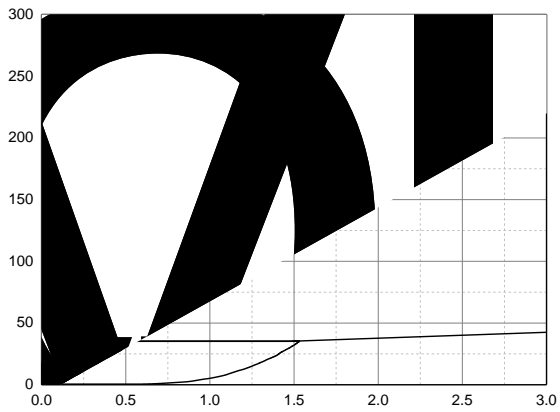
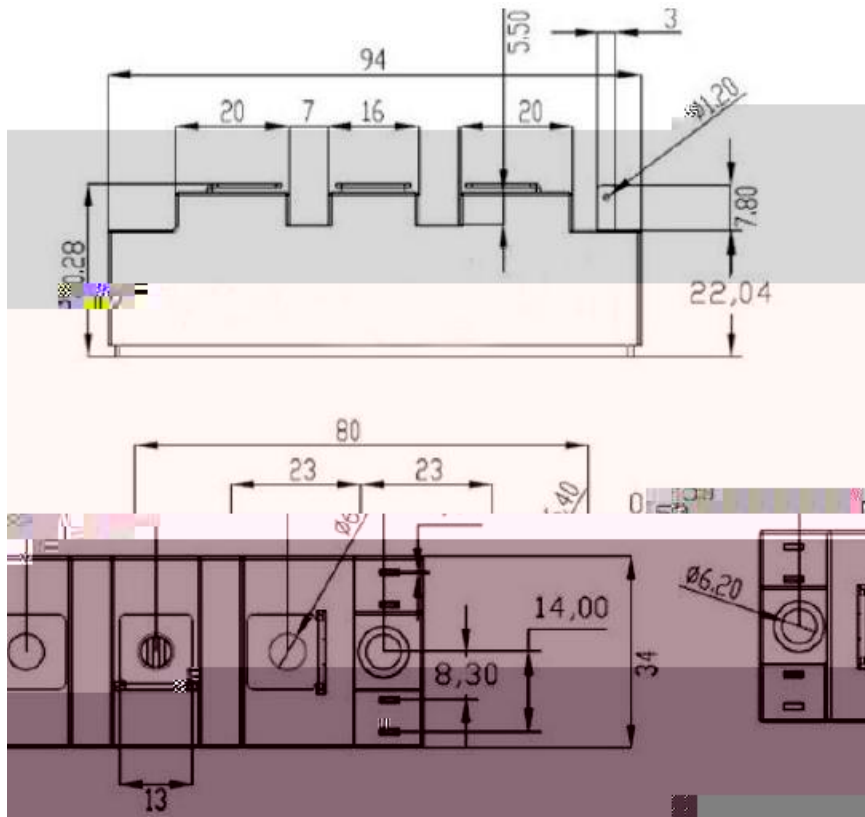


Fig. 9 Conduction characteristics of diode



Package Outline (Dimension in mm)



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